

***Amendments to the Claims***

1-13.(cancelled)

14.(previously presented) A semiconductor die package, comprising a semiconductor die and a permanent protective material surrounding substantially all of the die, the protective material fully curable by exposure to ultraviolet light and shrinking 10% or less by volume upon curing.

15.(previously presented) A semiconductor die package, comprising:  
a semiconductor die;  
conductive leads electrically connected to the die; and  
protective material covering substantially all of the die and at least a portion of the leads, the protective material fully curable by exposure to ultraviolet light and shrinking 10% or less by volume upon curing.

16.(previously presented) The semiconductor die package of Claim 15, wherein the protective material is formed from a mixture including a polymer resin and a photoactive compound.

17.(previously presented) The semiconductor die package of Claim 16, wherein the polymer resin comprises a phenol-formaldehyde epoxy novolac resin and the photoactive compound comprises triaryl sulfonium hexafluorophosphate.

18.(previously presented) The semiconductor die package of Claim 17, wherein the protective material is formed from a mixture including about 44% by volume phenol-formaldehyde epoxy novolac resin and about 1% by volume triaryl sulfonium hexafluorophosphate.

10/727,947

Response to Office Action

-2-

19.(currently amended) A method, comprising:  
coating substantially all of a semiconductor die with a polymer that is fully  
curable by exposure to ultraviolet light and shrinks 10% or less by volume upon curing;  
and  
fully curing the coating solely by exposing the coating to ultraviolet light.

20.(canceled)

21.(previously presented) A method, comprising:  
coating substantially all of a semiconductor die with a mixture of a phenol-  
formaldehyde epoxy novolac resin and triaryl sulfonium hexafluorophosphate; and  
exposing the coating to ultraviolet light.

22.(previously presented) The method of Claim 21, wherein coating comprises  
coating the semiconductor die with a mixture of about 44% by volume phenol-  
formaldehyde epoxy novolac resin and about 1% by volume triaryl sulfonium  
hexafluorophosphate.

23-25.(canceled)